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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

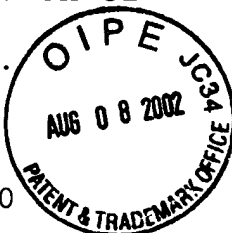
In the Patent Application of

Yukiyasu SUGANO et al.

Serial No. 09/478,812

Filed: January 7, 2000

For: Process For Producing Thin  
Film Semiconductor Device and  
Laser Irradiation Apparatus



Group Art Unit: 2815

Examiner: E. Lee

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AMENDMENT

Commissioner of Patents  
Washington, DC 20231

Sir:

In response to the Official Action mailed April 8, 2002,  
please amend the application as follows.

IN THE CLAIMS:

Sub 7  
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11. (amended) A thin film semiconductor device comprising  
a semiconductor thin film, a gate insulating film accumulated  
on one surface thereof, and a gate electrode accumulated  
entirely within a prescribed region of said semiconductor thin  
film through said gate insulating thin film,

wherein said semiconductor thin film is formed by forming  
a 30 to 80 nm layer of amorphous silicon or polycrystalline  
silicon having a first particle diameter on a substrate, and  
irradiating said substrate with an energy beam to convert said  
semiconductor thin film to polycrystalline silicon having a